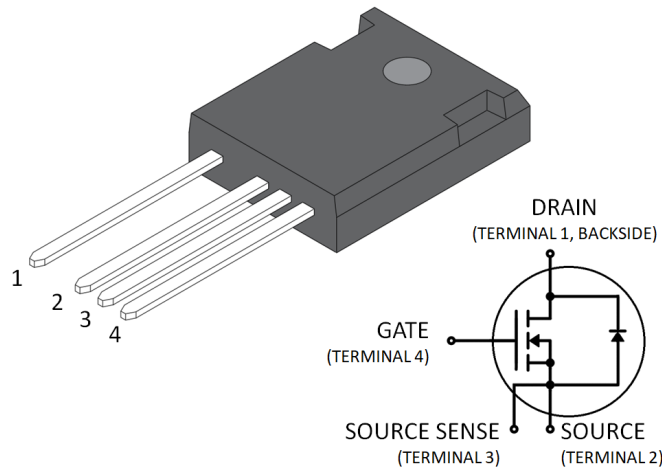


MSC080SMA120B4 Silicon Carbide N-Channel Power MOSFET

1 Product Overview

The silicon carbide (SiC) power MOSFET product line from Microsemi increases the performance over silicon MOSFET and silicon IGBT solutions while lowering the total cost of ownership for high-voltage applications. The MSC080SMA120B4 device is a 1200 V, 80 mΩ SiC MOSFET in a TO-247 4-lead package with a source sense.



1.1 Features

The following are key features of the MSC080SMA120B4 device:

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{j(max)} = 175\text{ }^{\circ}\text{C}$
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant

1.2 Benefits

The following are benefits of the MSC080SMA120B4 device:

- High efficiency to enable lighter, more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

1.3 Applications

The MSC080SMA120B4 device is designed for the following applications:

- PV inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- H/EV powertrain and EV charger
- Power supply and distribution

2 Device Specifications

This section shows the device specifications for the MSC080SMA120B4 device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the MSC080SMA120B4 device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{DS}	Drain source voltage	1200	V
I_D	Continuous drain current at $T_c = 25\text{ }^{\circ}\text{C}$	37	A
	Continuous drain current at $T_c = 100\text{ }^{\circ}\text{C}$	26	
I_{DM}	Pulsed drain current ¹	90	
V_{GS}	Gate-source voltage	23 to -10	V
P_D	Total power dissipation at $T_c = 25\text{ }^{\circ}\text{C}$	200	W
	Linear derating factor	1.33	W/ $^{\circ}\text{C}$

Note:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.

The following table shows the thermal and mechanical characteristics of the MSC080SMA120B4 device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		0.5	0.75	$^{\circ}\text{C}/\text{W}$
T_J	Operating junction temperature	-55		175	$^{\circ}\text{C}$
T_{STG}	Storage temperature	-55		150	
T_L	Soldering temperature for 10 seconds (1.6 mm from case)			260	
	Mounting torque, 6-32 or M3 screw			10	lbf-in
				1.1	N-m
Wt	Package weight		0.22		oz
			6.2		g

2.2 Electrical Performance

The following table shows the static characteristics for the MSC080SMA120B4 device. $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)\text{ DSS}}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ $I_D = 100\text{ }\mu\text{A}$	1200			V
$R_{DS(on)}$	Drain-source on resistance ¹	$V_{GS} = 20\text{ V}$ $I_D = 15\text{ A}$		80	100	m Ω
$V_{GS(th)}$	Gate-source threshold voltage	$V_{GS} = V_{DS}$ $I_D = 1\text{ mA}$	1.8	2.8		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold voltage coefficient	$V_{GS} = V_{DS}$ $I_D = 1\text{ mA}$		-4.5		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 1200\text{ V}$ $T_J = 25\text{ }^{\circ}\text{C}$ $V_{GS} = 0\text{ V}$			100	μA
		$V_{DS} = 1200\text{ V}$ $T_J = 125\text{ }^{\circ}\text{C}$ $V_{GS} = 0\text{ V}$			500	
I_{GSS}	Gate-source leakage current	$V_{GS} = 20\text{ V} / -10\text{ V}$			± 100	nA

Note:

1. Pulse test: pulse width < 380 μs , duty cycle < 2%.

The following table shows the dynamic characteristics for the MSC080SMA120B4 device. $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 4 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}$		838		pF
C_{rss}	Reverse transfer capacitance	$V_{DD} = 1000\text{ V}$ $V_{AC} = 25\text{ mV}$		9		
C_{oss}	Output capacitance	$f = 1\text{ MHz}$		84		
Q_g	Total gate charge	$V_{GS} = -5\text{ V}/20\text{ V}$		64		nC
Q_{gs}	Gate-source charge	$V_{DD} = 800\text{ V}$ $I_D = 15\text{ A}$		12		
Q_{gd}	Gate-drain charge			19		
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 800\text{ V}$		5		ns
t_r	Current rise time	$V_{GS} = -5\text{ V}/20\text{ V}$ $I_D = 15\text{ A}$		4		
$t_{d(off)}$	Turn-off delay time	$R_{G(ext)} = 4\text{ }\Omega^1$		21		
t_f	Current fall time	Freewheeling diode = MSC080SMA120B4		15		
E_{on}	Turn-on switching energy ²			266		μJ
E_{off}	Turn-off switching energy			52		
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 800\text{ V}$		4		ns
t_r	Current rise time	$V_{GS} = -5\text{ V}/20\text{ V}$ $I_D = 15\text{ A}$		4		
$t_{d(off)}$	Turn-off delay time	$R_{G(ext)} = 4\text{ }\Omega^1$		24		
t_f	Current fall time	Freewheeling diode = MSC010SDA120B		10		
E_{on}	Turn-on switching energy ²			166		μJ
E_{off}	Turn-off switching energy			50		
ESR	Equivalent series resistance	$f = 1\text{ MHz}$, 25 mV, drain short		1.9		Ω
SCWT	Short circuit withstand time	$V_{DS} = 960\text{ V}$, $V_{GS} = 20\text{ V}$		3		μs
E_{AS}	Avalanche energy, single pulse	$V_{DS} = 150\text{ V}$, $V_{GS} = 20\text{ V}$, $I_D = 15\text{ A}$		1000		mJ

Notes:

1. R_G is total gate resistance excluding internal gate driver impedance.
2. E_{on} includes energy of freewheeling diode.

2.3 Body Diode Characteristics

The following table shows the body diode characteristics for the MSC080SMA120B4 device. $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 5 • Body Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	$I_{SD} = 15\text{ A}$, $V_{GS} = 0\text{ V}$		4.0		V
V_{SD}	Diode forward voltage	$I_{SD} = 15\text{ A}$, $V_{GS} = -5\text{ V}$		4.2		V
t_{rr}	Reverse recovery time	$I_{SD} = 15\text{ A}$, $V_{GS} = -5\text{ V}$ $V_{DD} = 800\text{ V}$		34		ns
Q_{rr}	Reverse recovery charge	$dI/dt = -1000\text{ A}/\mu\text{s}$		200		nC
I_{rrm}	Reverse recovery current			6.5		A

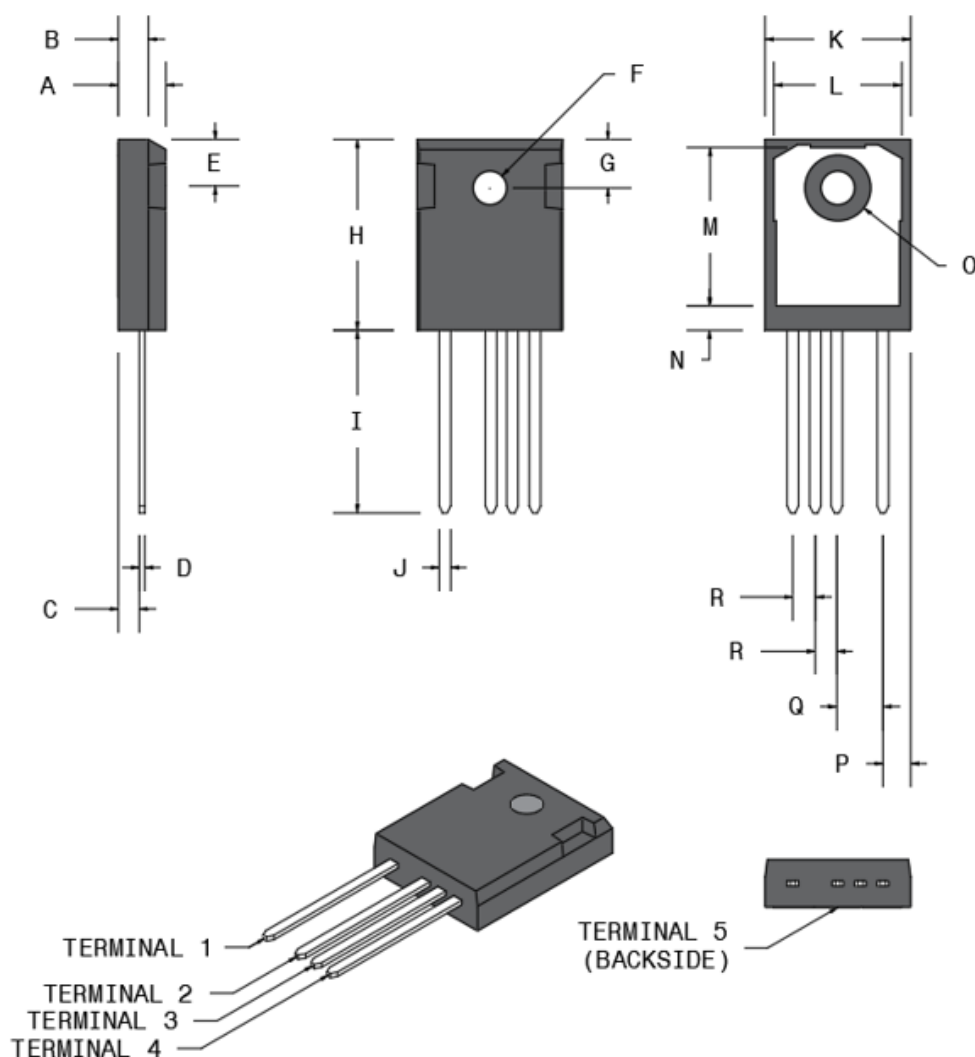
3 Package Specification

This section shows the package specification for the MSC080SMA120B4 device.

3.1 Package Outline Drawing

The following figure illustrates the TO-247 4-lead package outline of the MSC080SMA120B4 device. The dimensions in the figure below are in millimeters and (inches).

Figure 1 • Package Outline Drawing



The following table shows the TO-247 4-lead dimensions and should be used in conjunction with the package outline drawing.

Table 6 • TO-247-4L Dimensions

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
A	4.90	5.17	0.193	0.204
B	1.85	2.11	0.073	0.083
C	2.25	2.51	0.089	0.099
D	0.55	0.68	0.022	0.027
E	5.49	5.74	0.216	0.226
F	3.56	3.66	0.140	0.144
G	6.15 BSC		0.242 BSC	
H	20.83	21.08	0.820	0.830
I	19.81	20.32	0.780	0.800
J	1.07	1.33	0.042	0.052
K	15.77	16.03	0.621	0.631
L	13.89	14.15	0.547	0.557
M	16.25	16.85	0.640	0.663
N	2.00	2.75	0.079	0.108
O	7.10	7.50	0.280	0.295
P	2.87 BSC		0.113 BSC	
Q	5.08 BSC		0.200 BSC	
R	2.54 BSC		0.100 BSC	
Terminal 1	Drain			
Terminal 2	Source			
Terminal 3	Source sense			
Terminal 4	Gate			
Terminal 5	Drain			

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